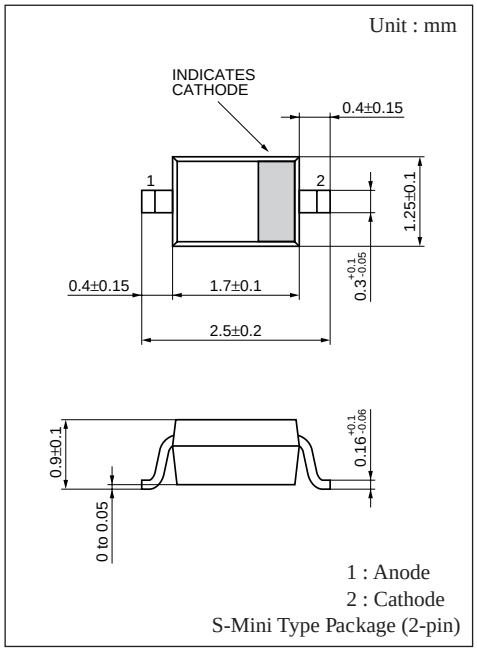
MA331

Silicon epitaxial planer type

■ Features

- Low series resistance r_D= 0.18Ω (typ.)
- Good linearity of C – V curve
- Small package, optimum for down-sizing of equipment



Marking Symbol : 6T

■ Absolute Maximum Ratings (Ta= 25˚C)

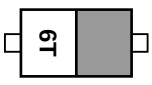
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	12	V
Forward current (DC)	I_F	20	mA
Junction temperature	T_j	150	˚C
Storage temperature	T_{stg}	– 55 to + 150	˚C

■ Electrical Characteristics (Ta= 25˚C)

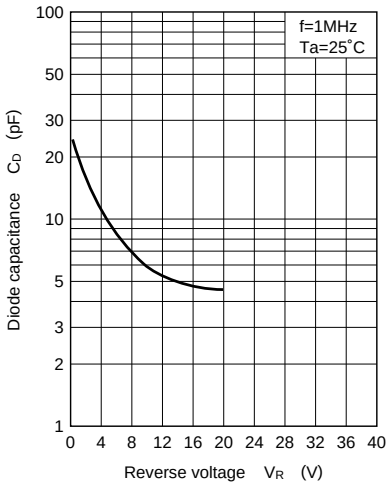
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R= 12V			10	nA
Diode capacitance	$C_{D(1V)}$	V_R= 1V, f= 1MHz	17.0		20.0	pF
	$C_{D(2V)}$	V_R= 2V, f= 1MHz	14.0	15.0	16.0	pF
	$C_{D(4V)}$	V_R= 4V, f= 1MHz	10.0		12.4	pF
	$C_{D(10V)}$	V_R= 10V, f= 1MHz	5.5	6.0	6.5	pF
Capacitance ratio	$C_{D(1V)}/C_{D(4V)}$		1.53	1.6	1.83	—
	$C_{D(2V)}/C_{D(10V)}$		2.25	2.5	2.75	—
Series resistance	r_D*	C_D= 9pF, f= 470MHz		0.18	0.22	Ω

Note 1. Rated input/output frequency : 470MHz
2. * [1] r_D measurement device : YHP MODEL 4191A RF IMPEDANCE ANALYZER

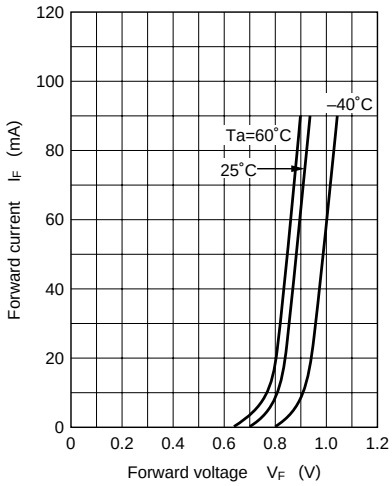
■ Marking



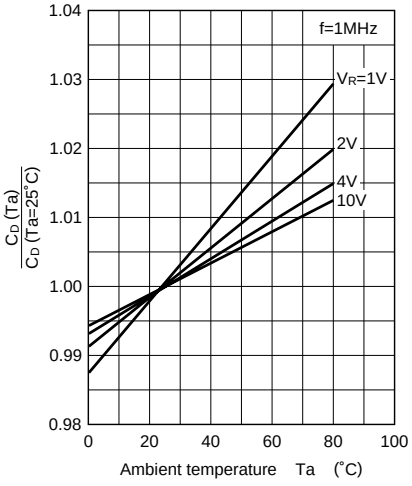
$C_D - V_R$



$I_F - V_F$



$C_D - Ta$



$I_R - Ta$